

#### **Features:**

- 1200V Schottky Diode
- Zero Reverse Recovery Current
- High Frequency Operation
- Positive Temperature Coefficient
- Temperature independent Switching

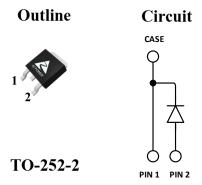
# **Applications:**

- Switch Mode Power Supply
- Booster diodes in PFC, DC/DC
- AC/DC converters

#### **Benefits:**

- Unipolar Rectifier
- Minimal switching loss
- Higher Efficiency
- Low cooling requirement

Symbol	Value	Unit		
$\mathbf{V}_{\mathbf{RRM}}$	1200	V		
$I_{F~(Tc=155^{o}C)}$	5	A		
Qc	27	пC		



### **Maximum Ratings**

Symbol	Parameter	Value	Unit	Test Conditions
$V_{R}$	DC Peak Reverse Voltage	1200	V	$T_J = 25^{\circ}C$
V <sub>RRM</sub>	Repetitive Peak Reverse	1200	V	$T_J = 25^{\circ}C$
V <sub>RSM</sub>	Surge Peak Reverse Voltage	1300	V	$T_J = 25^{\circ}C$
$I_{\mathrm{F}}$	Continuous Forward Current	16 7 5	A	$T_{\rm C} = 25^{\circ}{\rm C}$ $T_{\rm C} = 135^{\circ}{\rm C}$ $T_{\rm C} = 155^{\circ}{\rm C}$
I <sub>FRM</sub>	Repetitive Peak Forward Surge Current	24 17	A	$T_C = 25^{\circ}\text{C}$ , $T_P = 10\text{ms}$ , Half Sine Wave $T_C = 125^{\circ}\text{C}$ , $T_P = 10\text{ms}$ , Half Sine Wave
$I_{FSM}$	Non-Repetitive Peak Forward Surge Current	55 51	A	$T_C = 25^{\circ}\text{C}$ , $T_P = 10\text{ms}$ , Half Sine Wave $Tc = 125^{\circ}\text{C}$ , $T_P = 10\text{ms}$ , Half Sine Wave
P <sub>D</sub>	Power Dissipation	94 31	W	$T_{\rm C} = 25^{\circ}{\rm C}$ $T_{\rm C} = 125^{\circ}{\rm C}$
T <sub>J,max</sub>	Operating Junction Temperature	175	°C	
T <sub>stg</sub>	Storage Temperature Range	-55 to 175	°C	



### Thermal characteristics

Symbol	Parameter	Min.	Тур.	Max.	Unit
$ m R_{thJC}$	Thermal resistance		1.6		°C/W

### **Electrical Characteristics**

Symbol	Parameter	Value		T I \$4	Total Constitutions	
		Min.	Тур.	Max.	Unit	Test Conditions
V <sub>DC</sub>	DC Blocking Voltage	1200			V	$I_R = 100 \mu A, T_J = 25^{\circ} C$
$\mathbf{V_F}$	Forward Voltage		1.55	1.8	V	$I_F = 5A, T_J = 25^{\circ}C$
V F	rorward voltage		2.4	2.7		$I_F = 5A, T_J = 175^{\circ}C$
I <sub>R</sub>	Reverse Current		1	100	μΑ	$V_R = 1200V, T_J = 25^{\circ}C$
			15	500		$V_R = 1200V, T_J = 175^{\circ}C$
$\mathbf{Q}_{\mathrm{C}}$	Total Capacitive Charge		27		пC	$I_F = 5A$ , $dI/dt = 200A/\mu s$
						$T_J = 25^{\circ}C, V_R = 800V$
			262			$V_R = 1V, T_J = 25^{\circ}C, f = 1 \text{ MHz}$
C	Total Capacitance		23		pF	$V_R = 400V, T_J = 25^{\circ}C, f = 1 \text{ MHz}$
			19			$V_R = 800V, T_J = 25^{\circ}C, f = 1 \text{ MHz}$

## **Typical Performance**

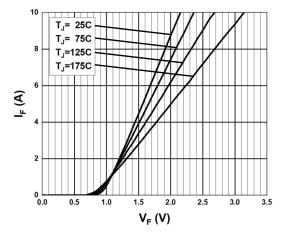


Fig. 1 Forward Characteristics

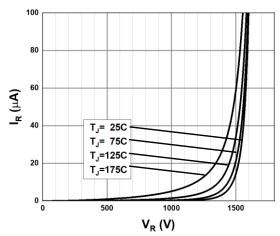


Fig. 2 Reverse Characteristics



### **Typical Performance**

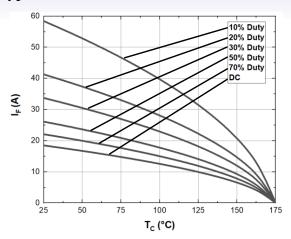


Fig. 3 Current Derating

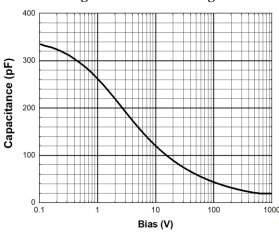


Fig. 5 Capacitance vs. Reverse Voltage

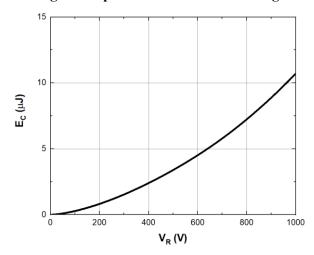


Fig. 7 Capacitance stored Energy

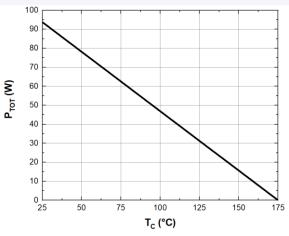


Fig. 4 Power Derating

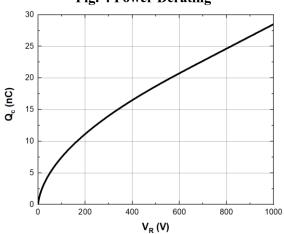
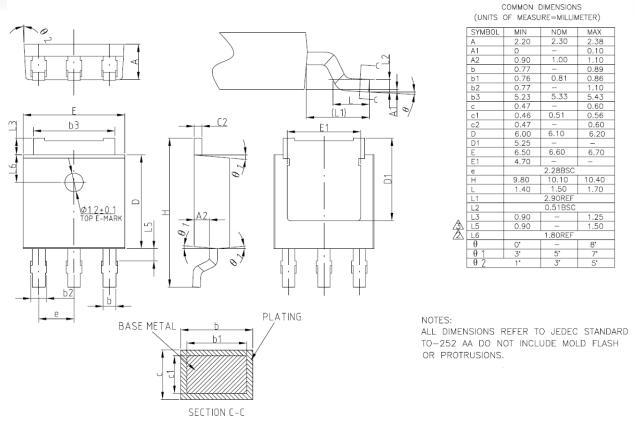


Fig. 6 Recovery Charge vs. Reverse Voltage



## Package TO-252-2 (Unit: mm)



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